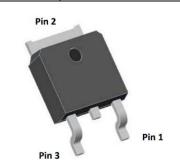
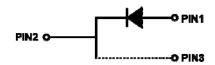




Silicon Carbide Schottky Diode

V_{RRM}	650V
I _{F (135°C)}	14A
Q _C	31nC





Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- AEC-Q101 qualified
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

• Package: TO-252

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Device marking code			D106510DXYG4
Reverse voltage (Repetitive peak) @ T _j =25°C	V_{RRM}	V	650
Reverse voltage (Surge peak) @ T _j =25°C	V_{RSM}	V	650
Reverse voltage (DC) @ T _j =25°C	V_{DC}	V	650
Continuous forward current @ T _C =25°C			31
Continuous forward current @ T _C =135°C	I _F	A	14
Continuous forward current @ T _C =152°C			10
Non-repetitive peak forward surge current @ T _C =25°C, tp=10ms, Half Sine Wave	I _{FSM}	Α	75
Power Dissipation@ T _C =25°C	В	W	119
Power Dissipation@ T _C =110°C	P _{TOT}	VV	51
i²t Value@ T _C =25°C ,tp=10ms	∫ i²dt	A ² S	28
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175

YJD106510DXYG4Q

■Electrical Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drop	V _F	٧	I _F =10A, T _j =25°C	1.35	1.60
			I _F =10A, T _j =175°C	1.75	-
Reverse current	I _R	μΑ	V _R =650V, T _j =25°C	0.5	25
			V _R =650V, T _j =175°C	5	-
Total capacitive charge	Qc	nC	V_R =400V, T_j =25°C , Q_C = $\int_0^{VR} C(V) dV$	31	-
Total capacitance	С	pF	V _R =0V, f=1MHZ	568	-
			V _R =200V, f=1MHZ	58	-
			V _R =400V, f=1MHZ	56	-
Capacitance stored energy	Ec	μJ	V _R =400V	4.8	-

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	R _{eJ-C}	°C W	1.26

■Typical Characteristics (Typical)

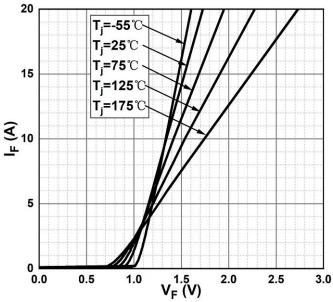


Figure 1. Forward Characteristics

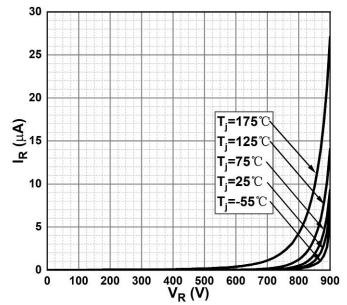
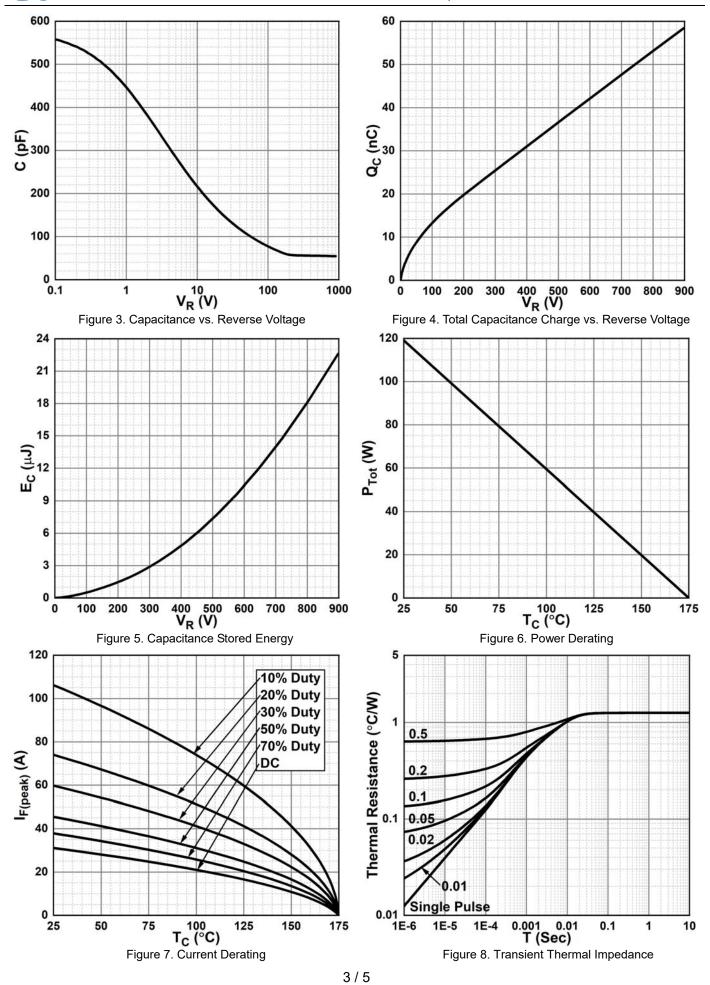


Figure 2. Reverse Characteristics

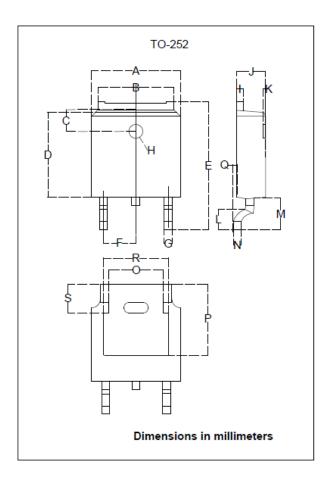
YJD106510DXYG4Q







■Outline Dimensions



TO-252				
Dim	Min	Max		
Α	6.500	6.700		
В	5.100	5.460		
С	1.400	1.800		
D	6.000	6.200		
E	10.000	10.400		
F	2.166	2.366		
G	0.660	0.860		
Н	Ф1.050	Ф1.350		
I	0.460	0.580		
J	2.200	2.400		
K	0	0.300		
L	0.890	2.290		
М	2.730	3.080		
N	0.430	0.580		
0	3.800	4.500		
Р	5.15	5.45		
Q	0	0.2		
R	4.50	5.10		
S	1.60	2.40		



YJD106510DXYG4Q

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